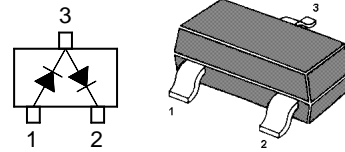


**Silicon Epitaxial Planar Switching Diode**
**Features**

- Fast switching speed
- High Conductance

**Applications**

- For general purpose switching


 Marking Code: **A7**  
 SOT-23 Plastic Package

**Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )**

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Reverse Voltage	$V_R$	100	V
Forward Current	$I_F$	200	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	1 2	A
		at $t = 1$ s at $t = 1$ $\mu$ s	
Power Dissipation	$P_d$	350	mW
Junction and Storage Temperature Range	$T_j, T_{stg}$	- 65 to + 150	$^\circ\text{C}$

**Characteristics at  $T_a = 25^\circ\text{C}$** 

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)R}$	100	-	V
Forward Voltage at $I_F = 1$ mA at $I_F = 10$ mA at $I_F = 100$ mA at $I_F = 150$ mA	$V_F$	0.55 0.67 0.75 -	0.7 0.82 1.1 1.25	V
Reverse Current at $V_R = 50$ V at $V_R = 100$ V at $V_R = 50$ V, $T_j = 125^\circ\text{C}$	$I_R$	- - -	1 3 100	$\mu\text{A}$
Total Capacitance at $V_R = 0$ V, $f = 1$ MHz	$C_T$	-	2	pF
Reverse Recovery Time at $I_F = I_R = 10$ mA, $I_{rr} = 0.1 \times I_R$ , $R_L = 100 \Omega$	$t_{rr}$	-	4	ns

